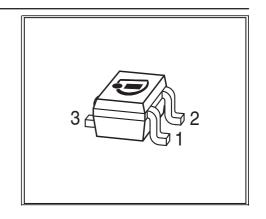


NPN Silicon RF Transistor

- For linear broadband amplifier application up to 500 MHz
- SAW filter driver in TV tuners
- Pb-free (RoHS compliant) package





Туре	Marking	Pin Configuration Package			Package
BF799W	LKs	1 = B	2 = E	3 = C	SOT323

Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V _{CEO}	20	V	
Collector-emitter voltage	V _{CES}	30		
Collector-base voltage	V_{CBO}	30		
Emitter-base voltage	V _{EBO}	3		
Collector current	I _C	35	mA	
Base current	I _B	10		
Total power dissipation	P _{tot}	280	mW	
<i>T</i> _S = 107 °C				
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-65 150		

Thermal Resistance

Junction - soldering point ¹⁾	R _{thJS}	≤ 155	K/W
------------------------------------------	-------------------	-------	-----

1

 $^{^{1}}$ For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified.

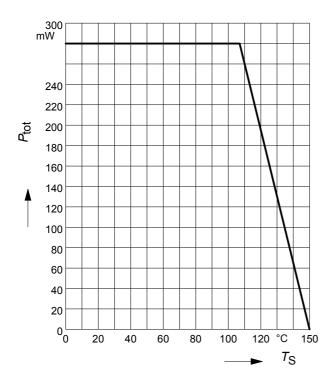
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics	•		•	•	
Collector-emitter breakdown voltage	V _{(BR)CEO}	20	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0					
Collector-base breakdown voltage	$V_{(BR)CBO}$	30	-	-	
$I_{\rm C}$ = 10 μ A, $I_{\rm E}$ = 0					
Base-emitter breakdown voltage	V _{(BR)EBO}	3	-	-	
$I_{\rm E}$ = 10 μ A, $I_{\rm C}$ = 0					
Collector-base cutoff current	/ _{CBO}	-	-	100	nA
$V_{\rm CB} = 20 \text{ V}, I_{\rm E} = 0$					
DC current gain	h _{FE}				-
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 10 V		35	95	_	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 10 V		40	100	250	
Collector-emitter saturation voltage	V _{CEsat}	-	0.1	0.3	V
$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 2 mA					
Base-emitter saturation voltage	V _{BEsat}	-	-	0.95	1
$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 2 mA					
AC characteristics			•	•	•
Transition frequency	f _T				MHz
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 10 V, f = 100 MHz		-	800	-	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 8 V, f = 100 MHz		-	1100	_	
Output capacitance	C _{ob}	-	0.96	-	pF
$V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = 0 \text{ mA}, f = 1 \text{ MHz}$					
Collector-base capacitance	C _{cb}	-	0.7	-	1
V _{CB} = 10 V, <i>f</i> = 1 MHz					
Collector-emitter capacitance	C _{ce}	-	0.28	-	1
V _{CE} = 10 V, <i>f</i> = 1 MHz					
Noise figure	F	-	3	-	dB
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 10 V, f = 100 MHz,					
$Z_{\rm S}$ = 50 Ω					
Output conductance	g _{22e}	-	60	-	μS
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 10 V, f = 35 MHz					

2

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Total power dissipation $P_{tot} = f(T_S)$



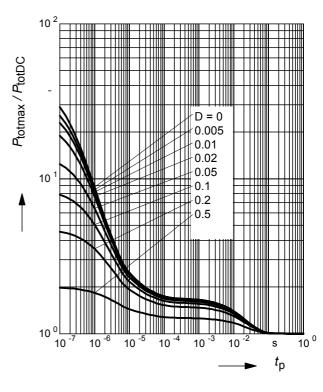
Permissible Pulse Load $R_{thJS} = f(t_p)$

10³ K/W 10² 10² 10¹ 0.5 0.2 0.1 0.05 0.02 0.01 0.005 D = 0 t_p

Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$$

3

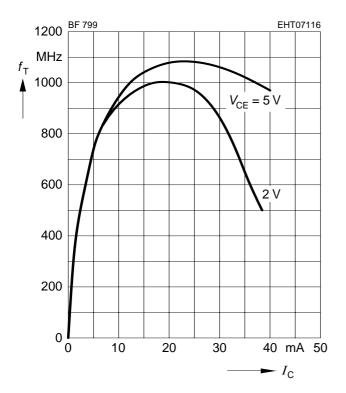


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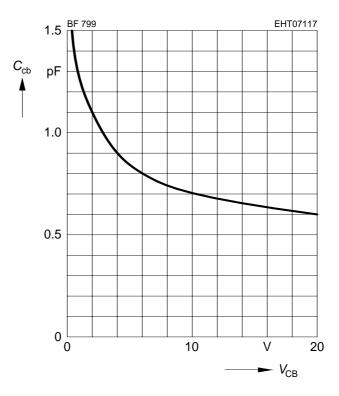


Transition frequency $f_T = f(I_C)$

f = 100MHz



Collector-base capacitance $C_{cb} = f(V_{CB})$ f = 1 MHz

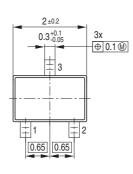


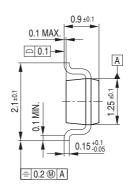
4



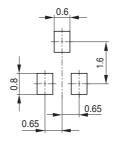
Package Outline



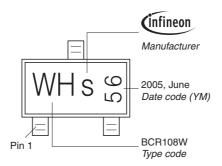




Foot Print

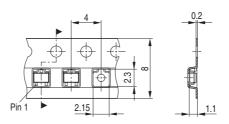


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel



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Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

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